

In the Claims:

Please amend the claims as follows:

1. (Currently Amended) ~~A Focusing~~ focusing device ~~[[1]]~~ with a refractive index profile changing from the center of the focusing device ~~[[1]]~~ towards its perimeter ~~[[3]]~~, ~~characterized in that wherein~~ wherein ~~[[the]]~~ a lateral refractive index distribution of the focusing device material is homogeneous and that the focusing device ~~[[1]]~~ comprises holes ~~[[2]]~~ for introducing a graded refractive index profile.
2. (Currently Amended) ~~The Focusing~~ focusing device according to claim 1, ~~characterized in that wherein~~ wherein the density of holes ~~[[2]]~~ increases towards the periphery of the focusing device ~~[[1]]~~.
3. (Currently Amended) ~~The Focusing~~ focusing device according to claim 1, ~~characterized in that wherein~~ wherein the holes ~~[[2]]~~ are distributed at random.
4. (Currently Amended) ~~The Focusing~~ focusing device according to claim 1, ~~characterized in that wherein~~ wherein the holes ~~[[2]]~~ are distributed according to a Monte Carlo algorithm.
5. (Currently Amended) ~~The Focusing~~ focusing device according to claim 1, ~~characterized in that wherein~~ wherein the focusing device ~~[[1]]~~ comprises at least two layers ~~[[16, 17, 18]]~~ deposited on a substrate ~~[[15]]~~.
6. (Currently Amended) ~~A Device~~ device comprising a focusing device according to claim 1.
7. (Currently Amended) ~~A Method~~ method of fabricating a planar focusing device ~~[[1]]~~, ~~characterized in that wherein~~ wherein a pattern of holes ~~[[2]]~~ arranged at random in a circular

area is defined by nano-imprint or lithography, in particular electron-beam lithography, on a layer structure and that the holes [(2)] thus defined are etched, in particular by reactive ion etching.

8. (Currently Amended) The Method method according to claim 7, ~~characterized in that~~ wherein the holes are distributed according to a generalized Monte Carlo algorithm.

9. (Currently Amended) The Method method according to claim 7, ~~characterized in that~~ wherein the holes are etched down to a substrate [(15)], in particular a silicon wafer.

10. (Currently Amended) The Method method according to claim 7, ~~characterized in that~~ wherein the holes [(2)] are patterned with a distance between holes [(2)] and diameters of the holes [(2)] in the sub-wavelength regime.